MITSUBISHI SEMICONDUCTOR <TRANSISTOR ARRAY>

POWEREX

M54564P/FP

8-UNIT 500mA SOURCE TYPE DARLINGTON TRANSISTOR ARRAY

DESCRIPTION

M54564P and M54564FP are eight-circuit output-sourcing Darlington transistor arrays. The circuits are made of PNP and NPN transistors. Both the semiconductor integrated circuits perform high-current driving with extremely low input-current supply.

FEATURES

- High breakdown voltage (BVcEo ≥ 50V)
- High-current driving (Io(max) = −500mA)
- With output pulldown resistance (Driving available with fluorescent display tube)
- Driving available with PMOS IC output or with TTL output
- Wide operating temperature range (Ta = -20 to +75°C)
- Output current-sourcing type

APPLICATION

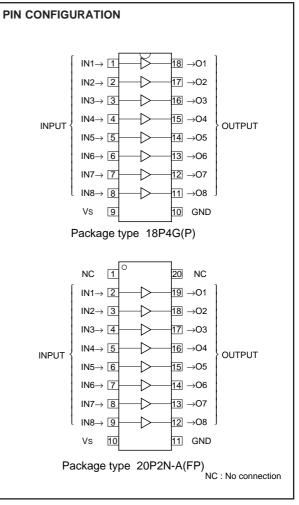
Drives of relays, printers, LEDs, fluorescent display tubes and lamps, and interfaces between MOS-bipolar logic systems and relays, solenoids, or small motors

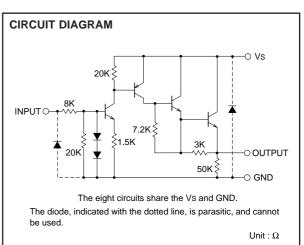
FUNCTION

The M54564P and M54564FP each have eight circuits, which are made of input inverters and current-sourcing outputs. The outputs are made of PNP transistors and NPN Darlington transistors. The PNP transistor base current is constant. Resistance of $50k\Omega$ is connected between each output pin and GND, making these ICs suitable for fluorescent display tubes. Vs and GND are used commonly among the eight circuits.

Output current is 500mA maximum. Supply voltage Vs is 50V maximum.

The M54564FP is enclosed in a molded small flat package, enabling space-saving design.









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ABSOLUTE MAXIMUM RATINGS (Unless otherwise noted, Ta = $-20 \sim +75$ °C)

Symbol	Parameter	Conditions	Ratings	Unit
VCEO	Collector-emitter voltage	Output, L	− 0.5 ~ + 50	V
Vs	Supply voltage		50	V
Vı	Input voltage		-0.5 ~ +30	V
lo	Output current	Current per circuit output, H	-500	mA
Pd	Power dissipation	Ta = 25°C, when mounted on board	1.79(P)/1.10(FP)	W
Topr	Operating temperature		− 20 ~ + 75	°C
Tstg	Storage temperature		− 55 ~ + 125	°C

RECOMMENDED OPERATING CONDITIONS (Unless otherwise noted, Ta = -20 ~ +75°C)

Symbol	Parameter		Limits			1.1-26
Syllibol			min	typ	max	Unit
Vs	Supply voltage		0	_	50	V
lo	Output current (Current per 1 circuit when 8 circuits	Duty Cycle P: no more than 8% FP: no more than 5%	0	_	-350	A
	are coming on si- multaneously)	Duty Cycle P: no more than 55% FP: no more than 30%	0	_	-100	mA
VIH	"H" input voltage		2.4	_	25	V
VIL	"L" input voltage		0	_	0.2	V

ELECTRICAL CHARACTERISTICS (Unless otherwise noted, $Ta = -20 \sim +75$ °C)

Symbol	Parameter	Test conditions	Limits			Unit
			min	typ*	max	Offic
IS (leak)	Supply leak current	Vs = 50V, VI = 0.2V	_	_	100	μΑ
V05 (+)	Collector-emitter saturation voltage	Vs = 10V, $VI = 2.4V$, $IO = -350mA$	_	1.6	2.4	V
VCE (sat)		Vs = 10V, $VI = 2.4V$, $IO = -100mA$	_	1.45	2.0	
lı.	Input current	VI = 5V, VS = 10V	_	0.4	0.7	mA
lı .		VI = 25V, VS = 30V	_	2.9	6.5	
Is	Supply current	Vs = 50V, VI = 5V	_	_	5.0	mA

^{*:} The typical values are those measured under ambient temperature (Ta) of 25°C. There is no guarantee that these values are obtained under any conditions.

SWITCHING CHARACTERISTICS (Unless otherwise noted, Ta = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			min	typ	max	Offic
ton	Turn-on time	CL = 15pF (note 1)	_	185	_	ns
toff	Turn-off time		_	4300	_	ns

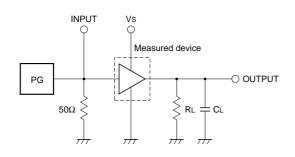


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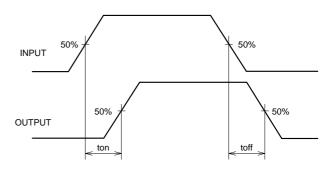
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NOTE 1 TEST CIRCUIT

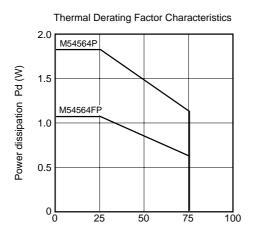


- (1) Pulse generator (PG) characteristics : PRR = 1kHz, tw = 10 μ s, tr = 6ns, tf = 6ns, Zo = 50 Ω Vi = 0 to 2.4V
- (2) Input-output conditions : $RL = 30\Omega$, Vs = 10V
- (3) Electrostatic capacity CL includes floating capacitance at connections and input capacitance at probes

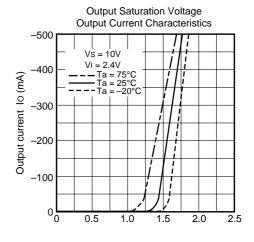
TIMING DIAGRAM



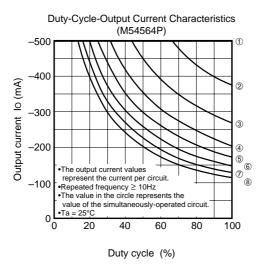
TYPICAL CHARACTERISTICS

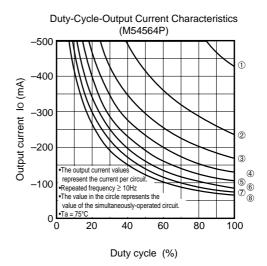






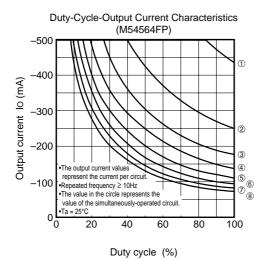
Output saturation voltage VCE (sat) (V)

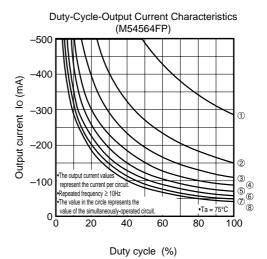




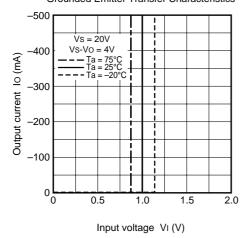
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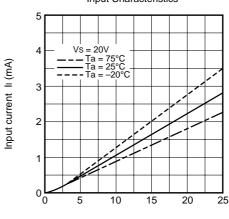












Input voltage VI (V)

